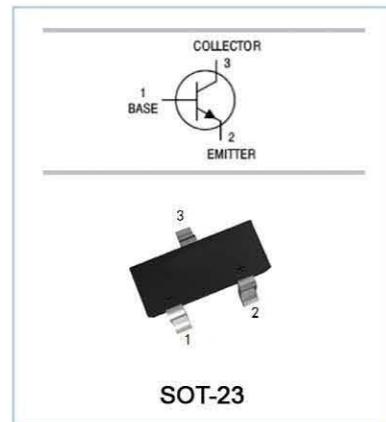


FEATURES

- High current gain bandwidth product.
- power dissipation.($P_c=200\text{mW}$)

APPLICATIONS

- NPN epitaxial silicon transistor.



MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

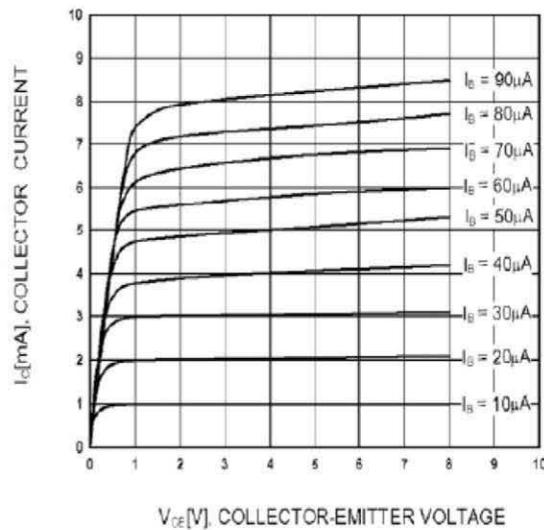
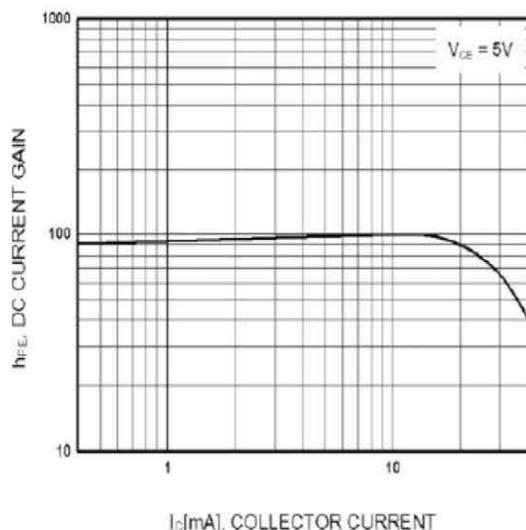
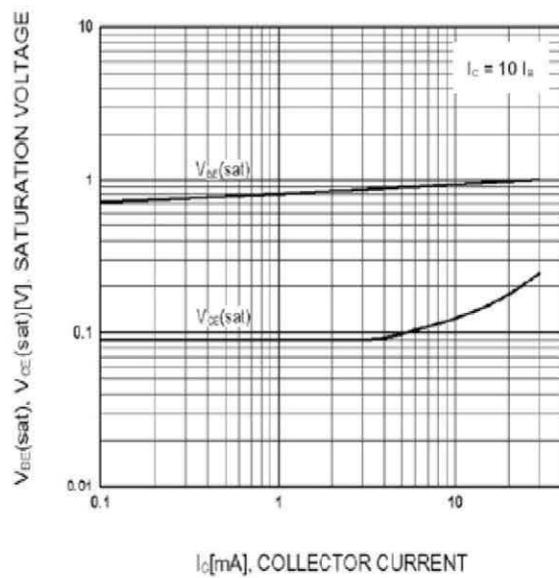
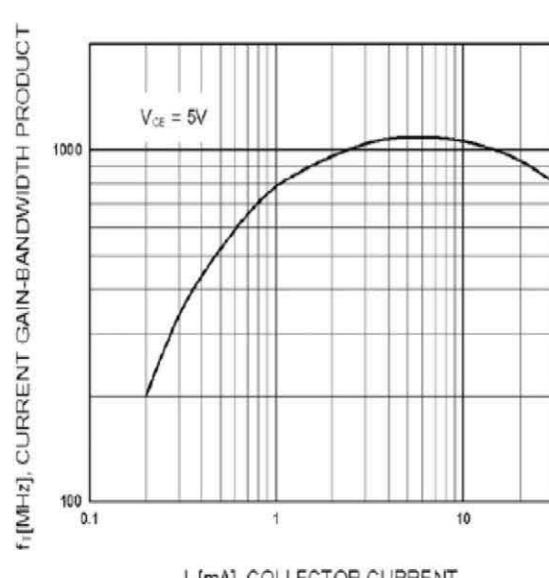
| Symbol | Parameter | Value | Units |
|----------------|----------------------------------|---------|-------|
| V_{CBO} | Collector-Base Voltage | 30 | V |
| V_{CEO} | Collector-Emitter Voltage | 18 | V |
| V_{EBO} | Emitter-Base Voltage | 4 | V |
| I_c | Collector Current -Continuous | 200 | mA |
| P_c | Collector Dissipation | 200 | mW |
| T_j, T_{stg} | Junction and Storage Temperature | -55~150 | °C |

ELECTRICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

| Parameter | Symbol | Test conditions | MIN | TYP | MAX | UNIT |
|--------------------------------------|----------------------|--|-----|-----|-----|---------------|
| Collector-base breakdown voltage | $V_{(BR)CBO}$ | $I_C=100\mu\text{A}, I_E=0$ | 25 | | | V |
| Collector-emitter breakdown voltage | $V_{(BR)CEO}$ | $I_C=0.1\text{mA}, I_B=0$ | 18 | | | V |
| Emitter-base breakdown voltage | $V_{(BR)EBO}$ | $I_E=-100\mu\text{A}, I_C=0$ | 4 | | | V |
| Collector cut-off current | I_{CBO} | $V_{CB}=20\text{V}, I_E=0$ | | | 0.1 | μA |
| Collector cut-off current | I_{CEO} | $V_{CE}=15\text{V}, I_B=0$ | | | 0.1 | μA |
| Emitter cut-off current | I_{EBO} | $V_{EB}=3\text{V}, I_C=0$ | | | 0.1 | μA |
| DC current gain | h_{FE} | $V_{CE}=5\text{V}, I_C =1\text{mA}$ | 40 | 200 | | |
| Collector-emitter saturation voltage | $V_{CE(\text{sat})}$ | $I_C=10 \text{ mA}, I_B= 1\text{mA}$ | | | 0.5 | V |
| Base-emitter saturation voltage | $V_{BE(\text{sat})}$ | $I_C=10 \text{ mA}, I_B= 1\text{mA}$ | | | 1.4 | V |
| Transition frequency | f_T | $V_{CE}=5\text{V}, I_C= 5\text{mA}$ $f=400\text{MHz}$ | 600 | | | MHz |

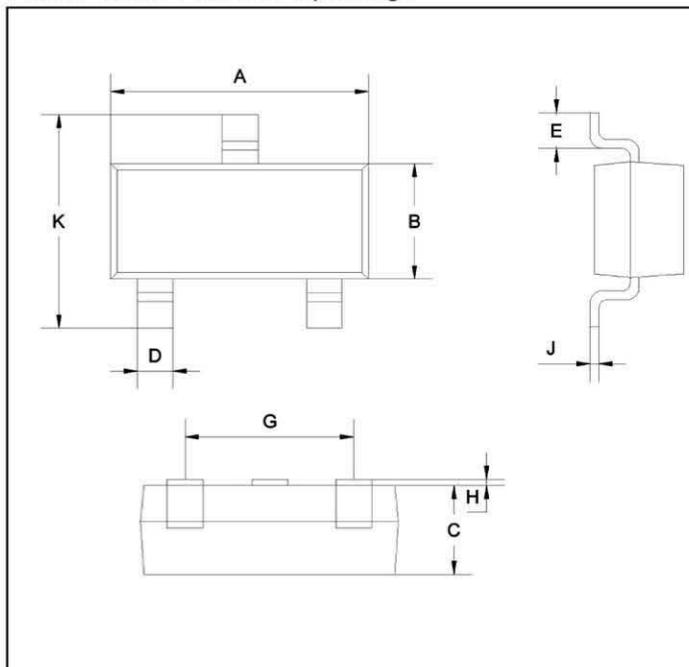
h_{FE}

| * | R | O | Y |
|----------|-------|--------|---------|
| h_{FE} | 40~80 | 70~140 | 100~200 |

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified

 V_{CE}[V], COLLECTOR-EMITTER VOLTAGE

 I_C[mA], COLLECTOR CURRENT

 I_C[mA], COLLECTOR CURRENT

 I_C[mA], COLLECTOR CURRENT

PACKAGE OUTLINE

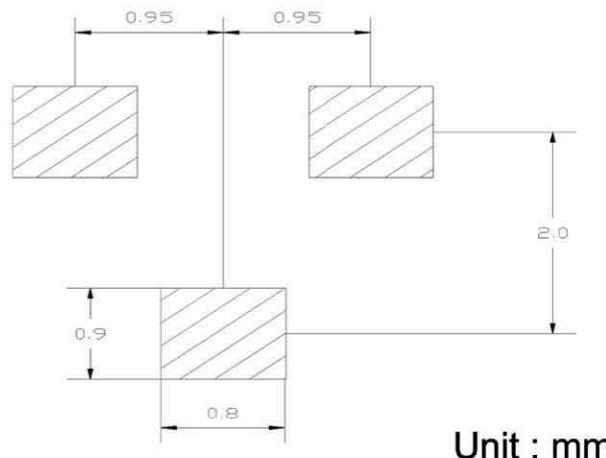
Plastic surface mounted package



| SOT-23 | | |
|--------|------------|------|
| Dim | Min | Max |
| A | 2.85 | 2.95 |
| B | 1.25 | 1.35 |
| C | 1.0Typical | |
| D | 0.37 | 0.43 |
| E | 0.35 | 0.48 |
| G | 1.85 | 1.95 |
| H | 0.02 | 0.1 |
| J | 0.1Typical | |
| K | 2.35 | 2.45 |

All Dimensions in mm

SOLDERING FOOTPRINT



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Shikues manufacturer:

Other Similar products are found below :

[619691C](#) [MCH4017-TL-H](#) [MJ15024/WS](#) [MJ15025/WS](#) [BC546/116](#) [BC556/FSC](#) [BC557/116](#) [BSW67A](#) [HN7G01FU-A\(T5L,F,T](#)
[NJVMJD148T4G](#) [NSVMMBT6520LT1G](#) [NTE187A](#) [NTE195A](#) [NTE2302](#) [NTE2330](#) [NTE2353](#) [NTE316](#) [IMX9T110](#) [NTE63](#) [NTE65](#)
[C4460](#) [SBC846BLT3G](#) [2SA1419T-TD-H](#) [2SA1721-O\(TE85L,F\)](#) [2SA1727TLP](#) [2SA2126-E](#) [2SB1202T-TL-E](#) [2SB1204S-TL-E](#) [2SC5488A-TL-H](#)
[2SD2150T100R](#) [SP000011176](#) [FMC5AT148](#) [2N2369ADCSM](#) [2SB1202S-TL-E](#) [2SC2412KT146S](#) [2SC4618TLN](#) [2SC5490A-TL-H](#)
[2SD1816S-TL-E](#) [2SD1816T-TL-E](#) [CMXT2207 TR](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [BC557B](#) [TTC012\(Q\)](#) [BULD128DT4](#) [JANTX2N3810](#)
[Jantx2N5416](#) [US6T6TR](#) [KSF350](#) [068071B](#)